

# Digital Microelectronic Circuits (361-1-3021)

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Lecture 7: Logical Effort



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### **Last Lectures**

#### □ The CMOS Inverter

- » Delay Calculation
- » Driving a Load
- CMOS Digital Logic
  - » Dealing with High Fan-In



### **This Lecture**

- So we learned how to drive a large load with a chain of inverters.
- □ But what if there is logic to be calculated along the way?
- How should we distribute the logic in order to optimally drive the load?
- Can we develop a methodology for designing a logical network?





### **Design Technique Question**

#### We need to implement an 8-input decoder: F = ABCDEFGH



#### □ Which implementation is best?



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## **Design Technique Question 2**

Is it better to drive a big capacitive load directly with the NAND gate or after some buffering?



Method to answer both of these questions:

# »Logical Effort

– This is an extension of the buffer sizing problem



### <u>**Reminder:</u>** Inverter with Load</u>

We saw that the delay increases with ratio of load to inverter size:



- $\Box t_{p0}$  is the intrinsic delay of an unloaded inverter. Load
- $\Box \gamma$  is a technology dependent ratio.
- □ *f* is the *Effective Fanout* ratio of load to inverter size



### **<u>Reminder</u>: Inverter with Load**

□ For easier equations, we will rewrite this a bit...

$$t_{pINV} \triangleq t_{p0} / \gamma = 0.69 R_{out} C_{in} \Longrightarrow \quad t_p = t_{pINV} (\gamma + f)$$

□ For a chain of inverters, we get:





### An Optimal (reference) Inverter



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### Now, lets look at a NAND Gate

- We will take a NAND gate sized for equal resistance to an optimal inverter.
- □ We notice that:



#### □ Let us write the delay of the NAND:

$$t_{p,NAND} = 0.69R_{NAND}C_{out} = 0.69R_{INV}\left(C_{out,NAND} + C_{Load}\right)$$



### Now, lets look at a NAND Gate



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### Now, lets look at a NAND Gate

□ We arrived at:

$$t_{p,NAND} = t_{p,INV} \left( 2\gamma + \frac{4}{3}f \right)$$

### □ Two Conclusions:

- » The intrinsic (unloaded) delay is twice that of an inverter.
- » The fanout increases the delay at a faster pace than an inverter.

### It is better to drive a load with an inverter than a NAND!

Ztrinu

### How about a NOR Gate?



A NOR gate is less efficient than a NAND at driving a load!



□ We can generalize the delay to be:

$$t_{p} = t_{p,INV} \left( p \cdot \gamma + LE \cdot f \right)$$

- » p intrinsic delay (~proportional to Fan In)
- » LE Logical Effort
- » f Electrical Effort

 $\gg LE(INV)=1 \quad p(INV)=1$ 

»  $EF = LExf \rightarrow Effective Fanout$ 

$$t_p = t_{p_1 p_2} \sqrt{8 + 3}$$



### □ To summarize:

- » The logical effort of a gate describes how much "effort" we need to perform a logic calculation.
- » An Inverter has the smallest logical effort and intrinsic delay of all static CMOS gates.
- » Logical Effort increases with gate complexity.



### **Generalization of LE**



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### **Generalization of LE**

$$t_{pd} = t_{p,inv} \left( p \cdot \gamma + LE \cdot f \right)$$

$$p \triangleq \frac{R_{gate}}{R_{inv}} \frac{C_{d,gate}}{C_{d,inv}} \qquad LE \triangleq \frac{R_{gate}}{R_{inv}} \frac{C_{g,gate}}{C_{g,inv}}$$



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## Logical Effort Methodology

**R**<sub>inv</sub>

d,gate

$$t_{pd} = t_{p,inv} \left( p \cdot \gamma + LE \cdot f \right)$$

- We "don't like" the resistance factor in the expressions for p and LE.
- Therefore, first size the gate so the resistance is equivalent to an optimal inverter.
- Now just find the ratio of capacitances to an optimal inverter!



gate

**R**<sub>in</sub>

g, gate

 $LE \triangleq$ 

### LE of a NAND Gate



### LE of a NOR Gate



### **Logical Effort of Gates**



### What happens with higher Fan-In?





### **Add Branching Effort**

□ What happens if a node branches off?



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### **Cascading gates into a Path**

$$t_{p} = t_{p,INV} \sum_{i=1}^{N} \left( p_{i} \cdot \gamma + \underbrace{LE_{i} \cdot f_{i} \cdot b_{i}} \right)$$

□ Let's give a few things names...

- » Stage Electrical Effort  $EF_i \equiv LE_i \cdot f_i \cdot b_i = LE_i \cdot \frac{C_{out,i} \cdot b_i}{C_{in,i}}$ » Path Electrical Fanout  $F \equiv \frac{C_{out}}{C_{in}}$ » Path Logical Effort  $\Pi LE = LE_1 \cdot LE_2 \cdot \ldots \cdot LE_N$
- » Path Branching Effort  $\Pi B = b_1 \cdot b_2 \cdot \ldots \cdot b_N$

» Path Effort 
$$PE = F \cdot \prod LE \cdot \prod B$$



### **Cascading gates into a Path**

$$t_p = t_{p,INV} \sum_{i=1}^{N} \left( p_i \cdot \gamma + LE_i \cdot f_i \cdot b_i \right)$$

- Using the same approach as before, we can find the minimal delay.
- The solution, again, is that the electrical effort should be equal between stages, so we get:

$$EF_i = \sqrt[N]{PE} = \sqrt[N]{F \cdot \Pi LE \cdot \Pi B}$$



□ We now have a delay equation:

$$t_p = N \cdot \sqrt[N]{PE} + \gamma \sum p_i$$

□ We can find the optimal number of stages.



### Summary – Method of Logical Effort



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